
The Latest Progress in Model-Based Mask Data Preparation

Linyong (Leo) Pang

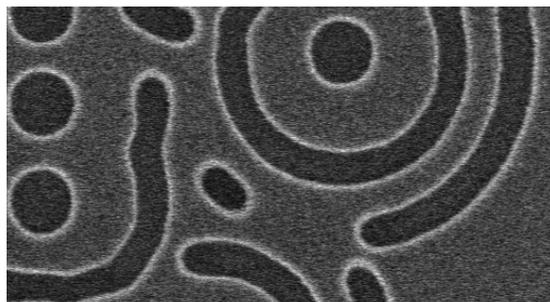
Bo Su

D2S, Inc.

A Decade of ILT!



2005



6

Papers

2

Foundries

1

Memory

1

Mask shop



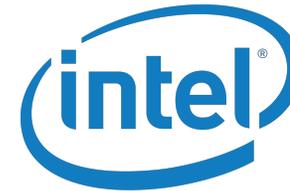
Enter the complex mask...

ILT Adopted as the Way Forward



>200

Papers



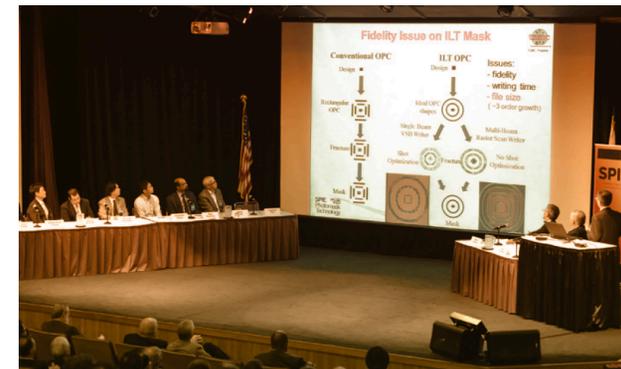
台灣積體電路製造股份有限公司
Taiwan Semiconductor Manufacturing Company, Ltd.

Officially
announced

Today



台灣積體電路製造股份有限公司
Taiwan Semiconductor Manufacturing Company, Ltd.



ILT expertise proliferated

2014 panel

Complex Masks Pose Challenges



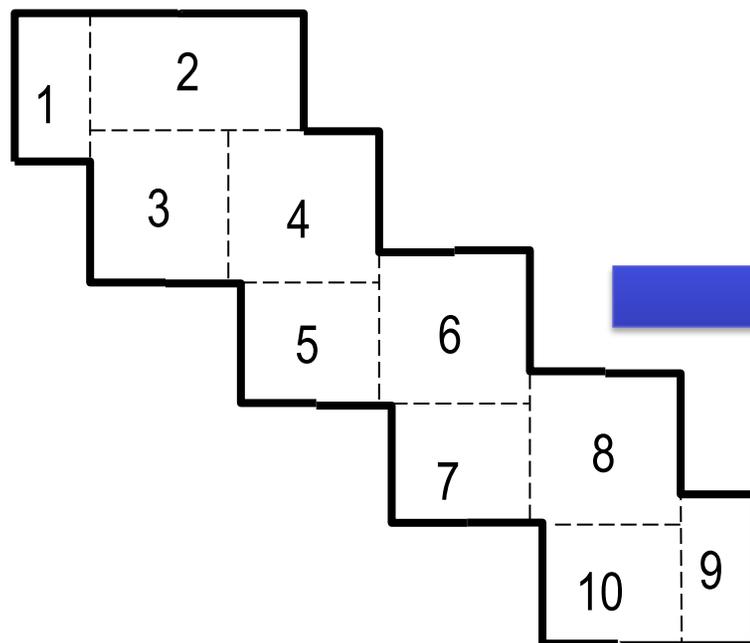
Long VSB write-times



Low accuracy
due to proximity effect

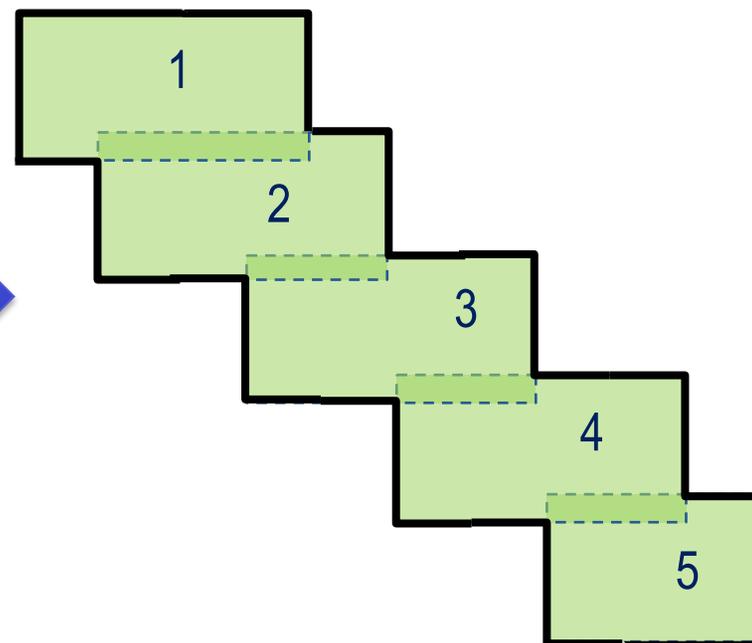
Overlapping Shots = Reduced Shot Count

10 conventional shots



5 overlapping shots

Plus, extra energy in overlapping areas



Overlapping shots cast more energy in less mask-writing time:

= Better process margin

= Better CDU

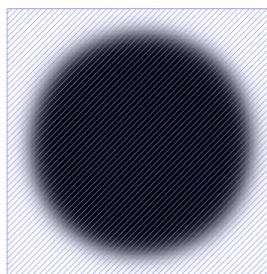
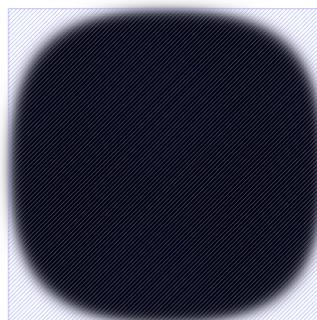
= No mask-write time vs. mask-quality compromise

eBeam Needs Proximity Correction

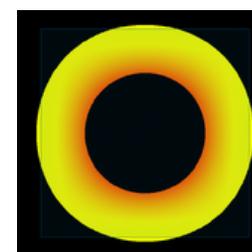
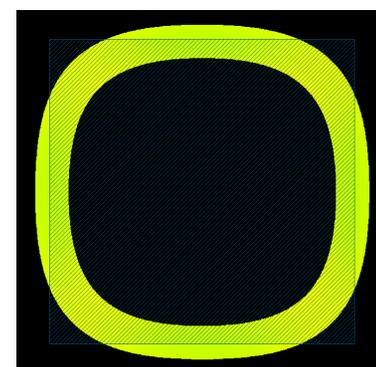
Shot Size



Exposed Resist



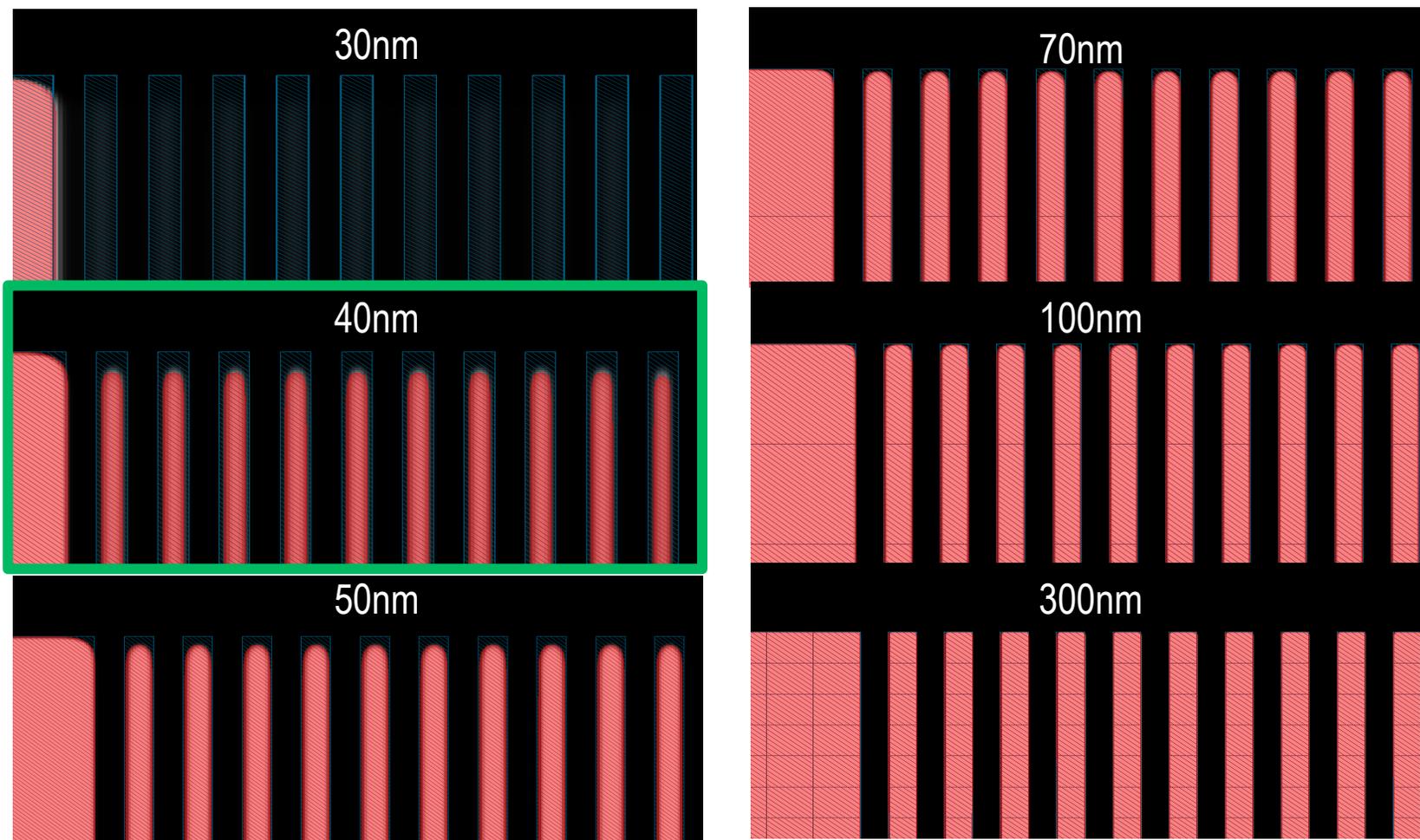
Edge Slope



**Bad
Dose
Margin**

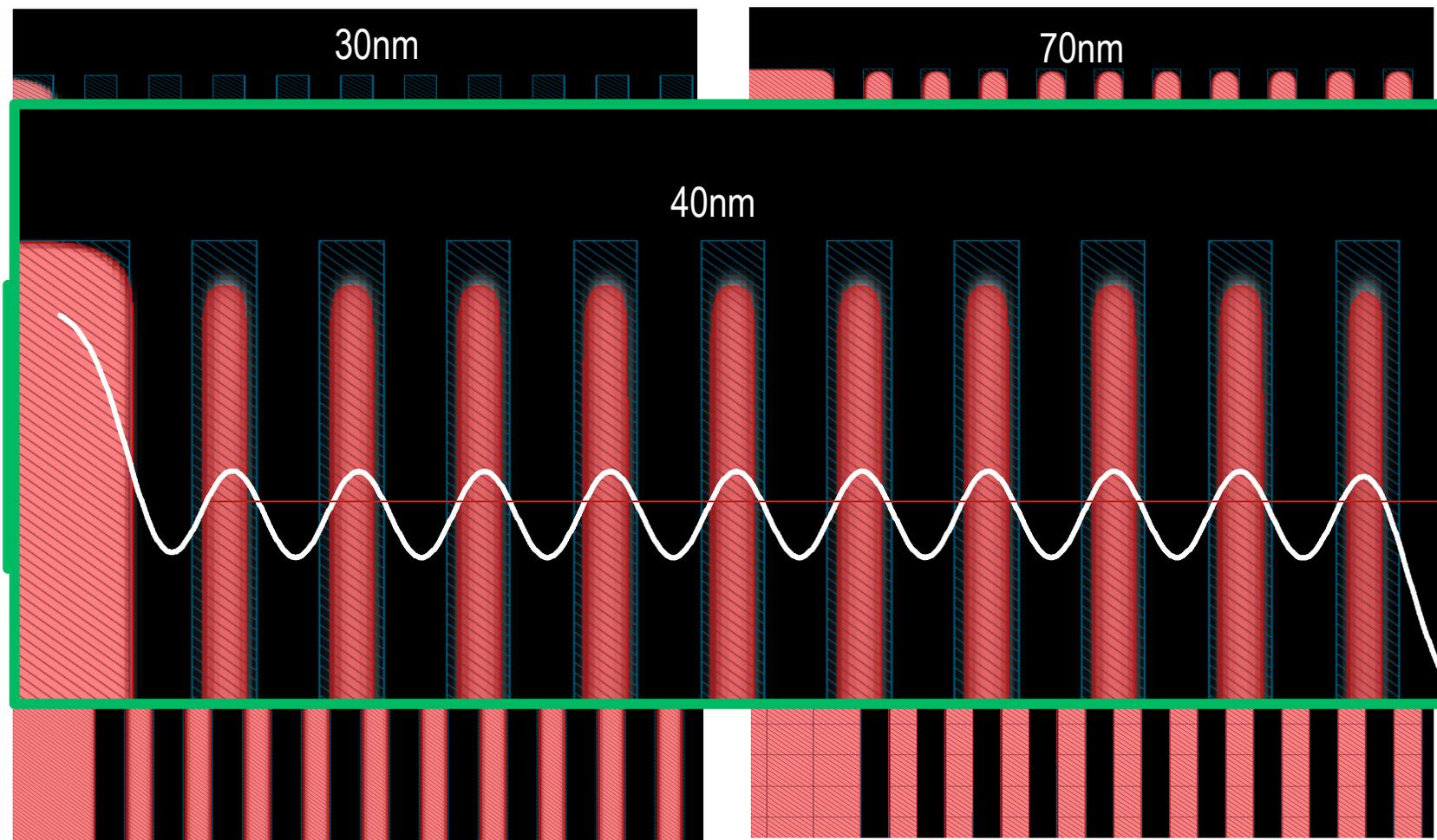
- At 20nm node, eBeam writing is no longer “faithful”
- Needs proximity correction, like OPC at 90/65nm
- Dose margin is the problem

< 50nm, Context is Critical



Pictures enlarged to show contour

< 50nm, Context is Critical



Pictures enlarged to show contour

Model-Based MDP is the Answer for ILT

- Above 50nm, context-independent, rules-based processing works well enough
- Below 50nm, context is critical
- If we can't push below 40nm, we leave the benefits of Moore's Law on the table
- Simulation-based mask processing is the answer

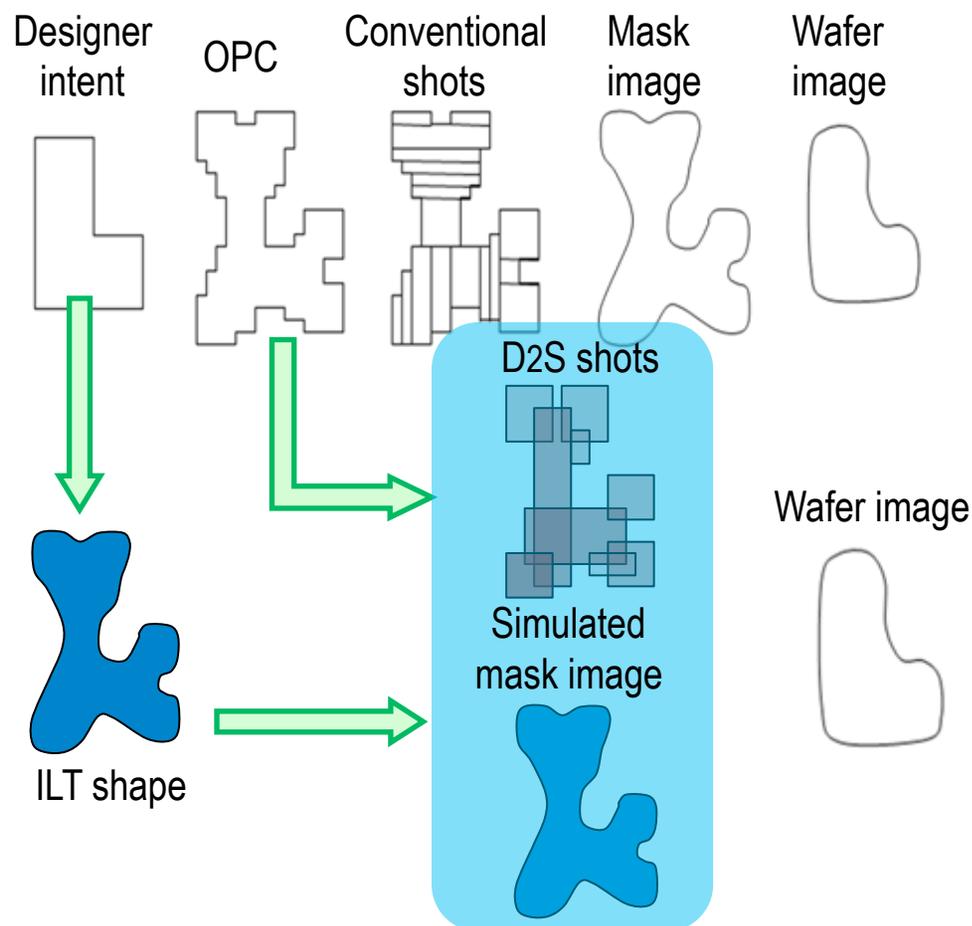
MB-MDP, Overlapped Shots Required with VSB for Complex Masks

Conventional solution:

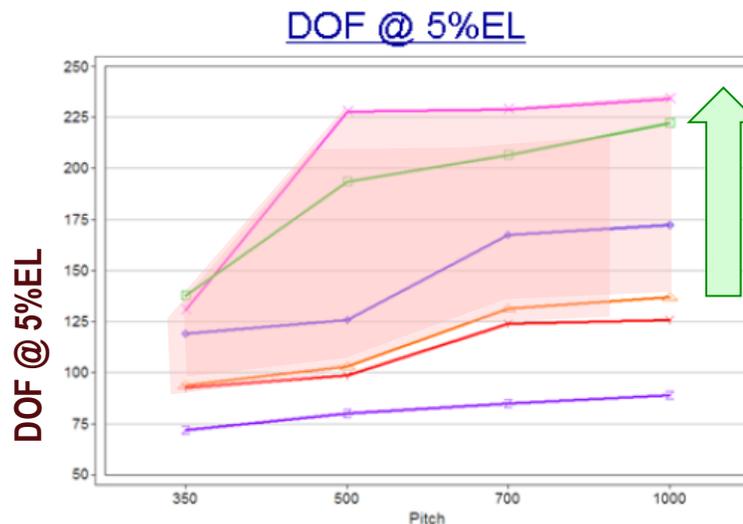
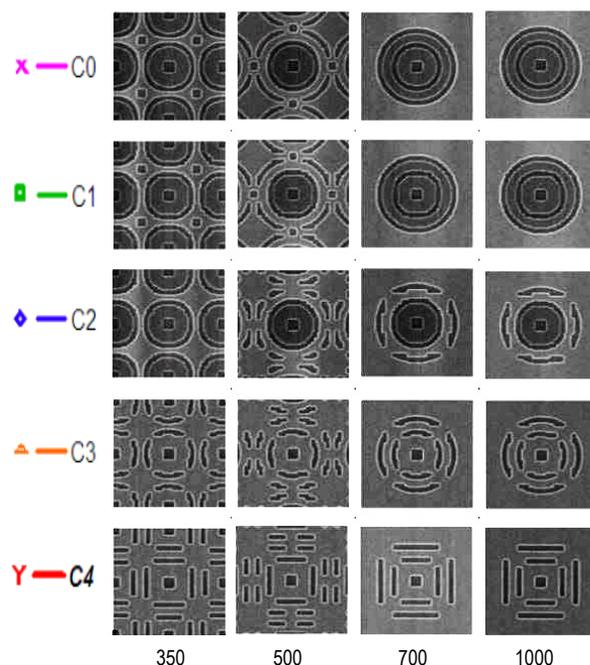
- Geometry-based
- Shots cover OPC layout without overlapping
- Higher shot count and worse mask fidelity

D2S solution:

- Model-based, better CDU control
- Overlapping shots to maximize shot contribution to the final mask shapes
- Lower shot count and better mask fidelity

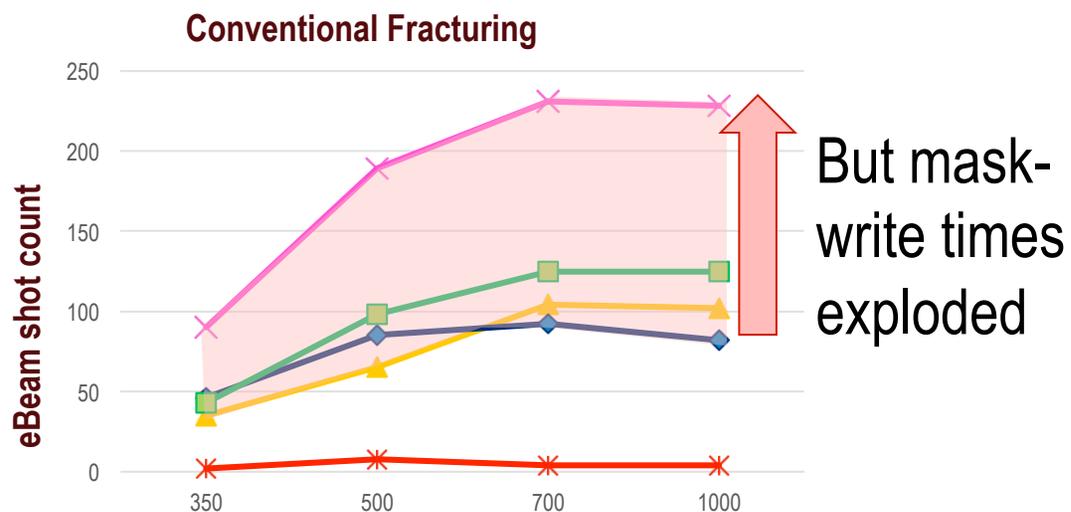
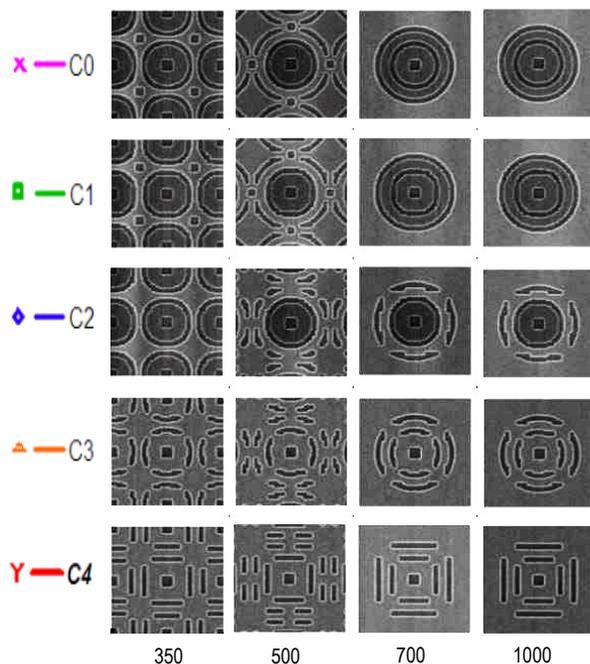


Complex Shapes are only Feasible with MB-MDP and Overlapped Shots



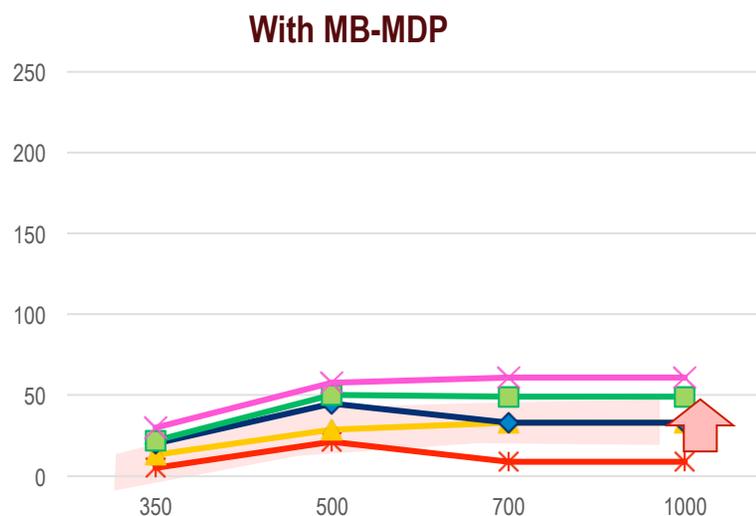
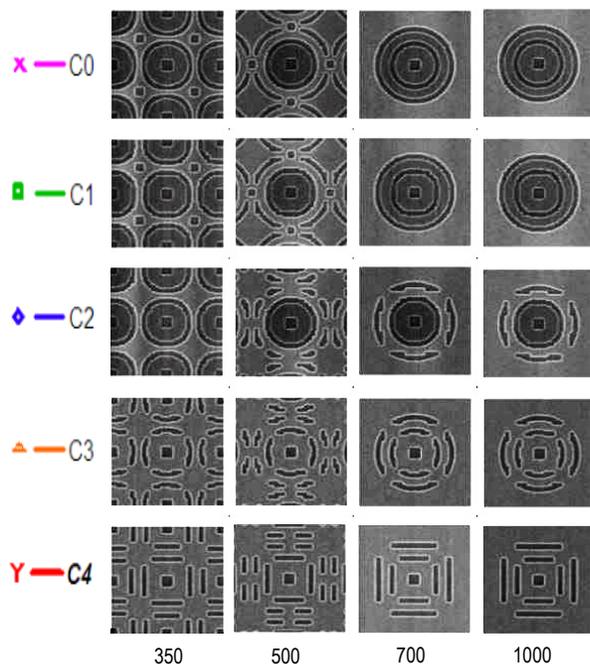
Much better DOF possible with unconstrained shapes

Complex Shapes are only Feasible with MB-MDP and Overlapped Shots



The base study on conventional fracturing is courtesy of Byung-Gook Kim, et al., PMJ 2009

Complex Shapes are only Feasible with MB-MDP and Overlapped Shots



Mask-write times do not explode with MB-MDP

Benefits of MB-MDP Proven at Key Customer Sites

“Enabler for the next generation mask process”

Head of customer OPC team

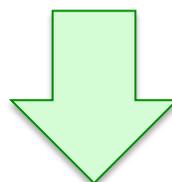
1.5nm

18%



CDU

40%



ILT
Write Time
reduction

Model
Fitting
1D

MB-MDP is Recognized by Industry Leaders at Semicon Taiwan 2015

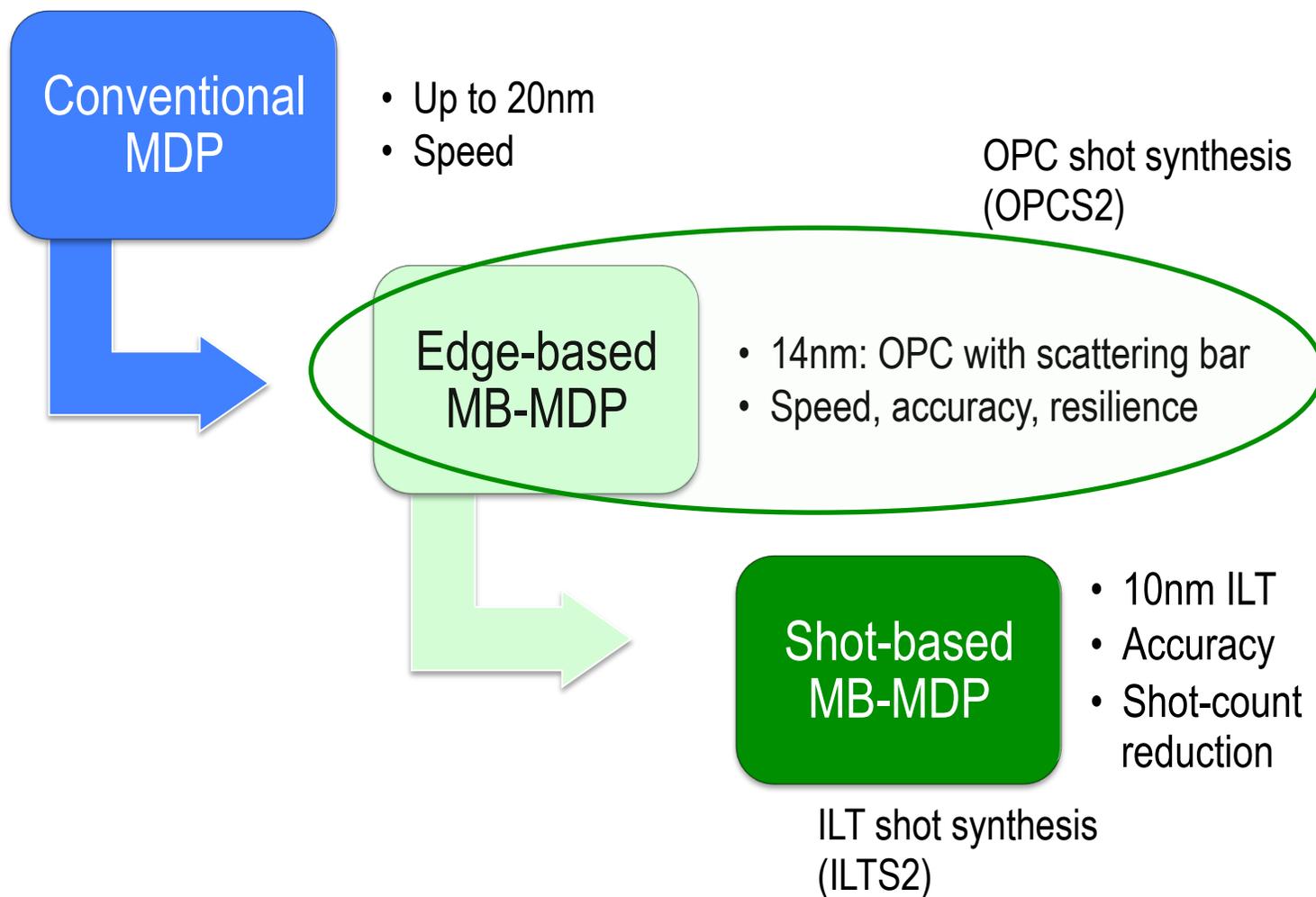
	Opening Speech with Market Overview: Infrastructure for IoT (PDF Download) Dr. An Steegen, Senior Vice President Process Technology, imec
	EUV Lithography for Sub-10-nm CMOS Technology (PDF Download) Dr. Anthony Yen, Director, TSMC
	EUV Lithography Insertion (PDF Download) Dr. Kars Troost, Senior Product Manager, ASML
14:55-15:20	Break
	A Computer Science Perspective on Computational Challenges for Sub-10nm Mask Synthesis (Not Authorized) Mr. Srinivas Raghvendra, Vice President, Synopsys
	Computational Lithography Technology for Foundry (Not Authorized) Dr. Ru-Gun Liu, Deputy Director, TSMC
	Removing the Last Road Block of Deploying ILT into 10nm Node by Model-based Mask Data Preparation and Overlapped Shots (PDF Download) Dr. Leo Pang, Chief Product Officer and Executive VP, D2S

“Innovative mask technology by D2S”

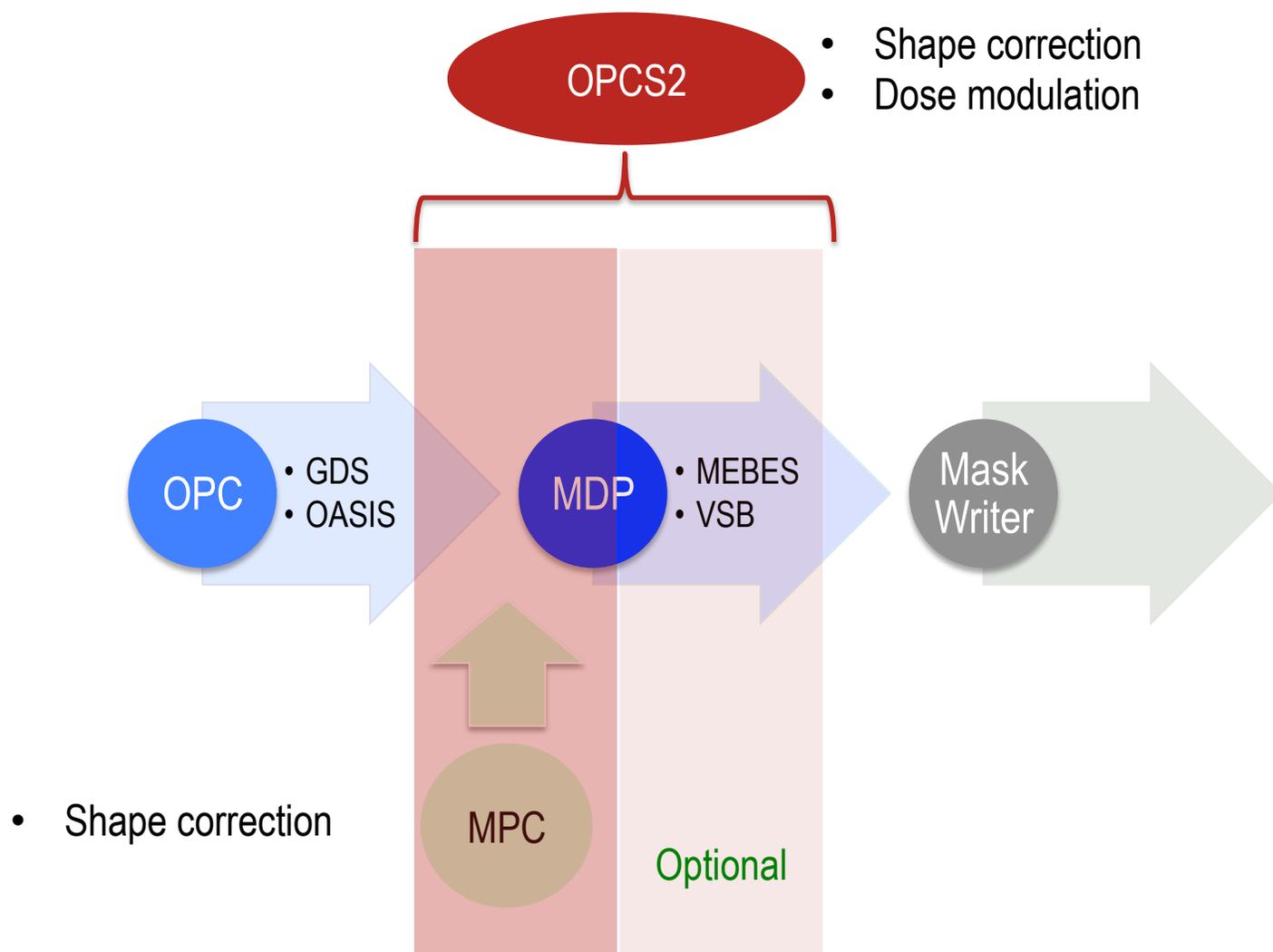


TSMC
Deputy Director
Dr. Ru-Gun Liu

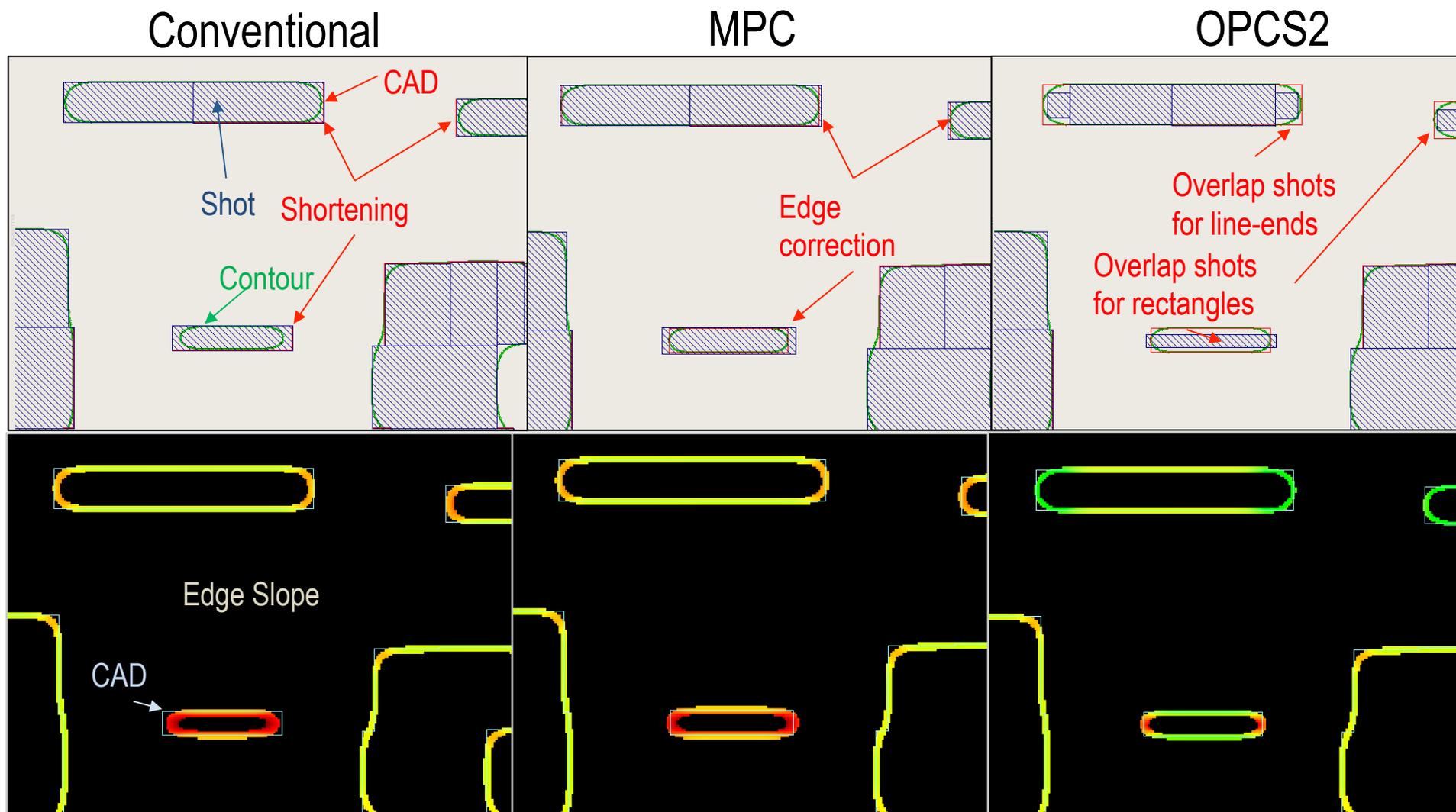
New Edge-Based Correction Feature Added to MB-MDP for Non-ILT Masks



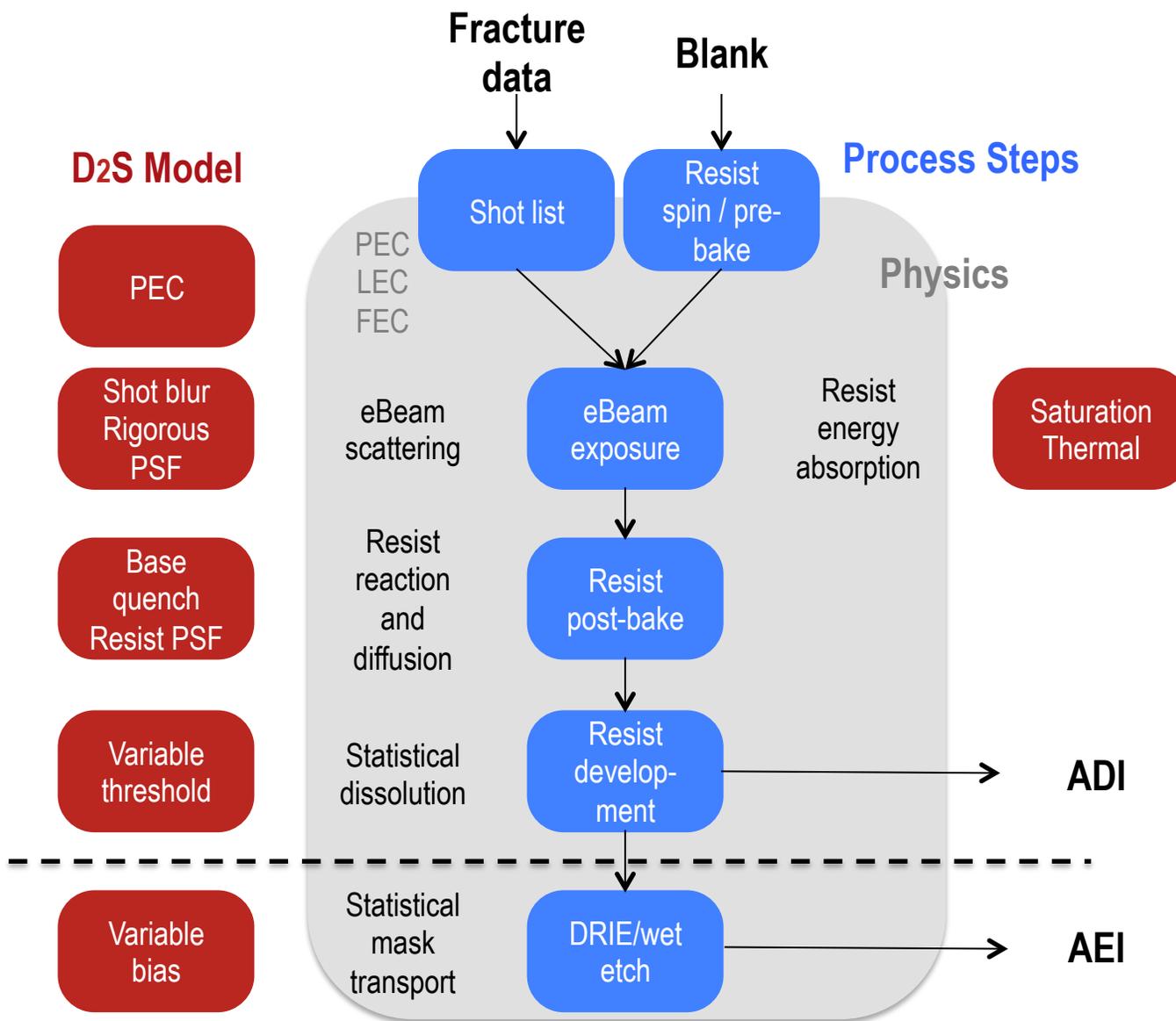
OPCS2 = MPC+ Dose Modulation + (Conventional MDP)



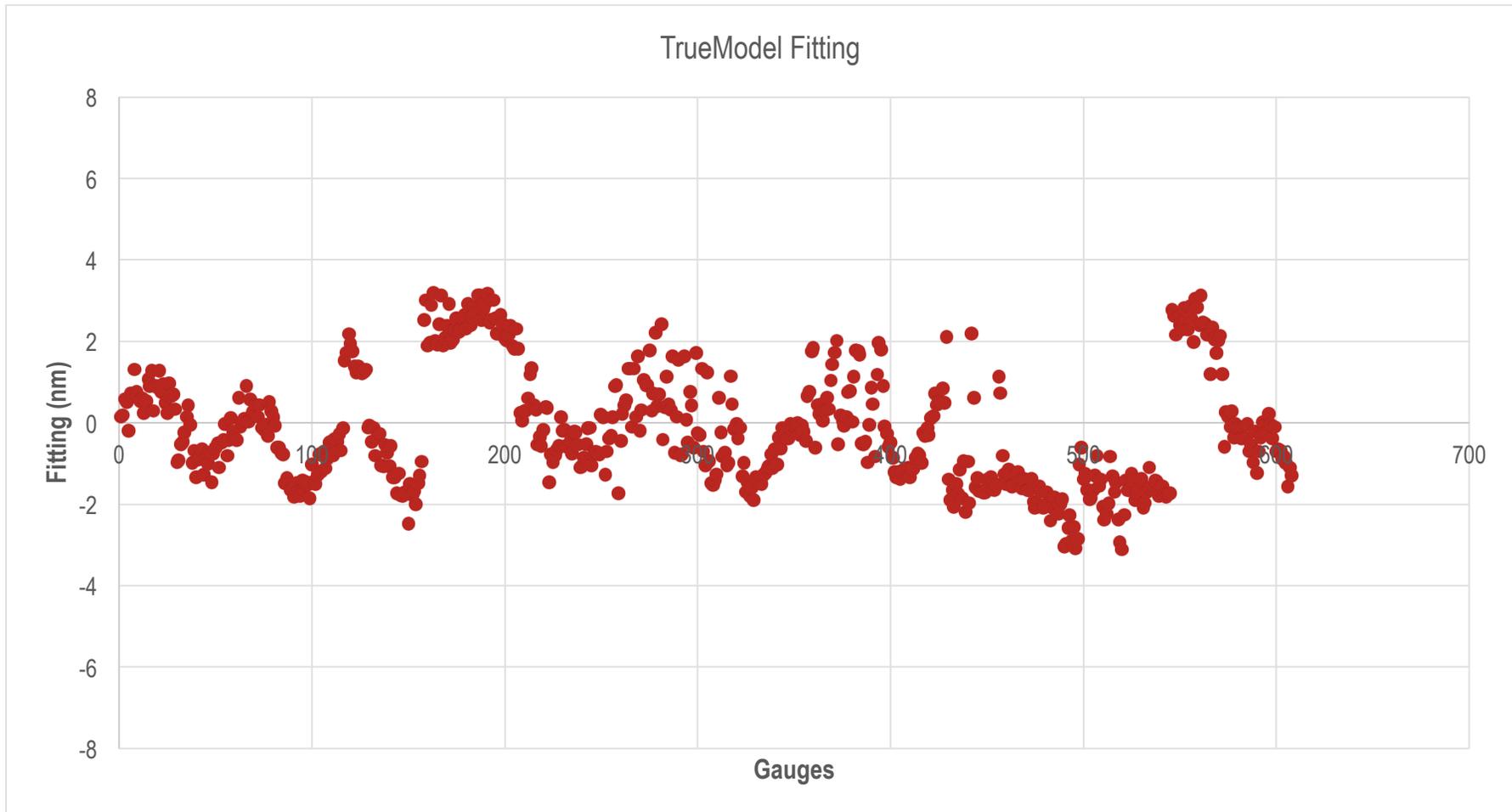
OPCS2 Efficiently Improves SRAF Printing and Linearity for Normal OPC



The Mask Model is the Key



D2S Mask Model is Reaching 1.5nm RMS



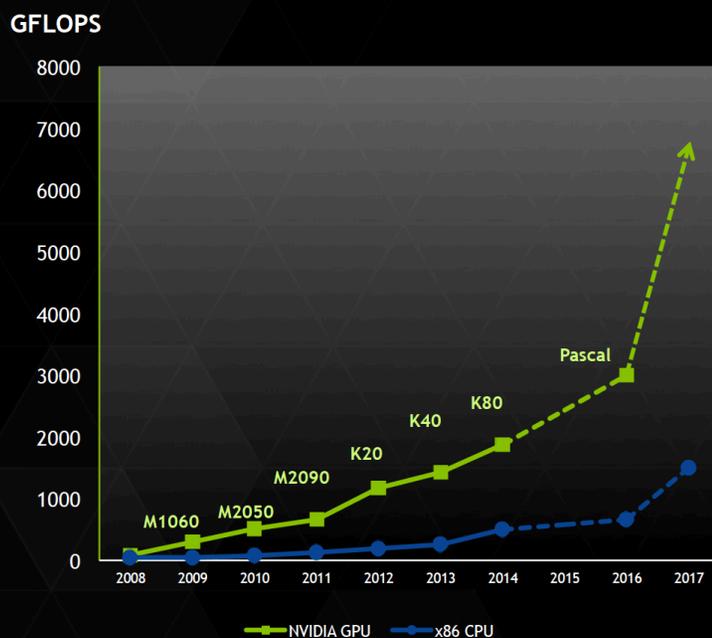
Is MB-MDP Run Time Ready for Production Use?

- Over 100X more computation than MB-OPC
- Mask scale 4X than wafer scale
 - Imagine calculation on every 1nm on wafer scale
- Requires optimization on fracturing
 - Break the OPC pattern into shots
- Has to consider overlapped shots
- eBeam proximity effect has short (nm), mid, and long range (mm)
- Full mask vs full chip: 10X bigger

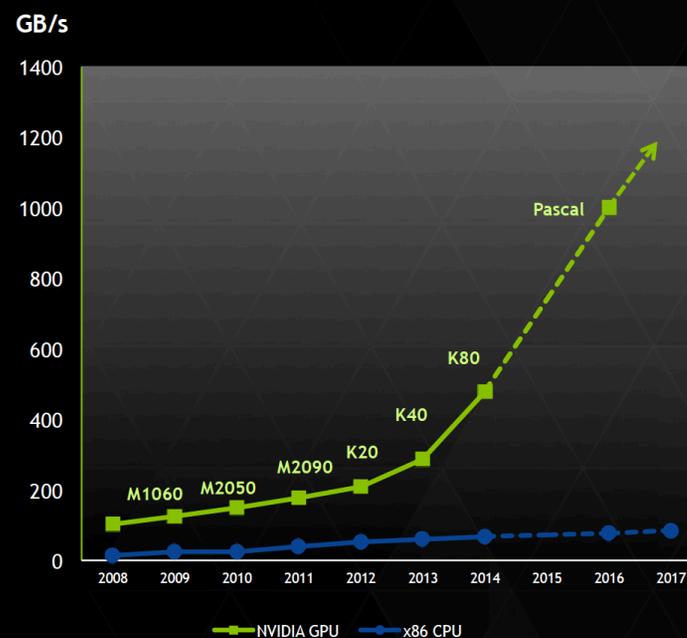
Scientific Computing Is Moving to GPU

PERFORMANCE GAP CONTINUES TO GROW

Peak Double Precision FLOPS



Peak Memory Bandwidth



Jen-Hsun Huang, CEO of NVIDIA, GPU Technology Conference, 2015

D2S 400TFLOPS CDP Using GPUs Is In Production Use at Mask Shops

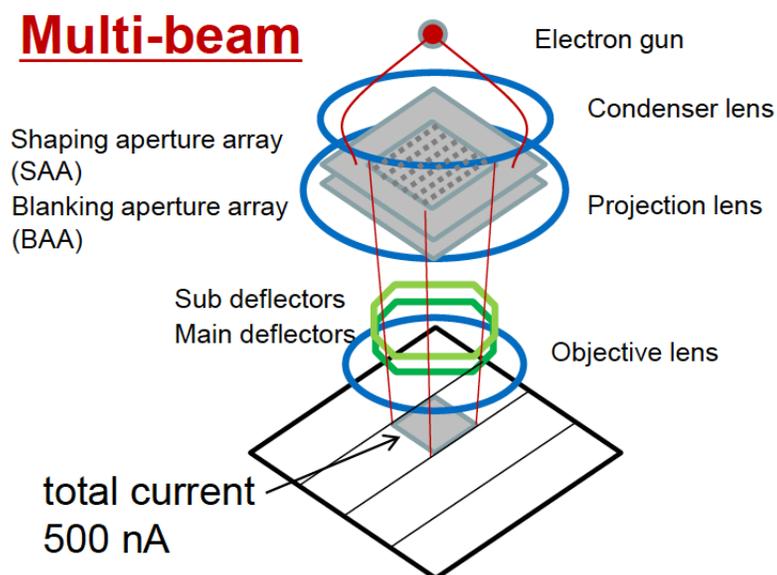


- 400 TFLOPS
- In production use
- Part of NuFlare EBM 9500
- Simulates the entire mask plane
- All standard parts, with built-in redundancy

D2S Computational Design Platform (CDP)

Multi-Beam Mask Writer Will Need MB-MDP Even More

- Multi-beam mask writer is the ultimate answer for ILT
 - Write-time independent of mask complexity
 - Use slower resist
 - Smaller features
- It requires MB-MDP
 - Large data set to process
 - Needs dose modulation



H. Matsumoto, 2016 Introduction and recent results of Multi-beam mask writer MBM-1000, SPIE 2016 eBeam Initiative Luncheon Event

MB-MDP is Being Deployed in Production

- ILT is being deployed in production at the leading edge
- Mask makers are faced with ILT masks
- Overlapped shots and MB-MDP enable VSB mask writer to write complex ILT masks
- Scientific computing is moving to GPU
- GPU-accelerated MB-MDP can meet the speed requirement of mass production
- Multi-beam mask writer will require MB-MDP, too

